

line 5, before "formed" insert --is--;
line 7, after "substrate" delete "; and a"
and insert therefor --. A--;

line 7, before "filled" insert --is--;

Page 6, line 3, delete "11" and insert therefor
--111--;

Page 7, line 1, delete "owing" and insert therefor
--due--;

IN THE CLAIMS:

1. (Once Amended) A dynamic random access memory having a trench capacitor, said memory comprising:

a semiconductor substrate of one conduction type;

a trench formed in said semiconductor substrate;

a first conductive layer formed on a deep portion [the]
of an inner surface of said trench and not being formed in
[except for] a region [adjacent] close to [the opening portion]
an entrance of said trench;

a dielectric layer being formed on said first conductive layer [exposed] in said trench and being formed on
said inner [the] surface of said trench in said region close to
said entrance of said trench [said semiconductor substrate];

a second conductive layer [filled] filling in said trench through said dielectric layer;

said first conductive layer, said dielectric layer, and said second conductive layer constituting a storage capacitor;
and